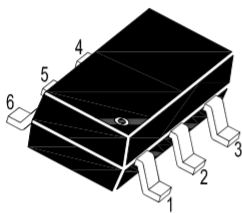


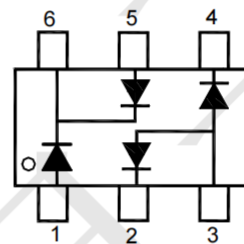
Features

- High speed
- High switching speed



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1. A1 2. K1 3. CA
4. K2 5. A2 6. CC

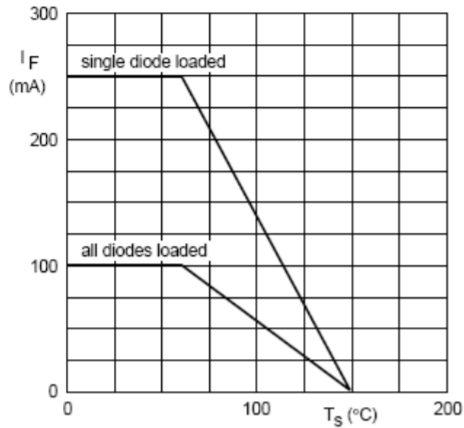


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

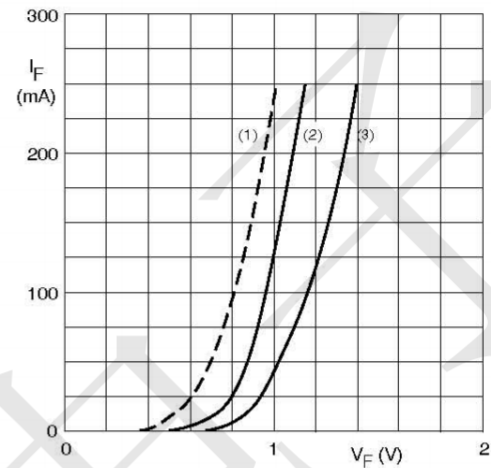
Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Reverse Voltage	V_R	75	V
Continuous Forward Current	I_F	Single Diode Loaded 250	mA
		All Diodes Loaded 100	
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	at $t = 1 \mu\text{s}$ 4	A
		at $t = 1 \text{ms}$ 1	
		at $t = 1 \text{s}$ 0.5	
Total Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	- 65 to + 150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1 \text{mA}$ at $I_F = 10 \text{mA}$ at $I_F = 50 \text{mA}$ at $I_F = 150 \text{mA}$	V_F	0.715	V
		0.855	
		1	
		1.25	
Reverse Current at $V_R = 25 \text{V}$ at $V_R = 75 \text{V}$ at $V_R = 25 \text{V}$, $T_j = 150^\circ\text{C}$ at $V_R = 75 \text{V}$, $T_j = 150^\circ\text{C}$	I_R	30	nA
		2.5	μA
		60	μA
		100	μA
Diode Capacitance at $V_R = 0$, $f = 1 \text{MHz}$	C_d	2	pF
Reverse Recovery Time at $I_F = I_R = 10 \text{mA}$, $I_{rr} = 0.1 \times I_R$, $R_L = 100 \Omega$	t_{rr}	4	ns

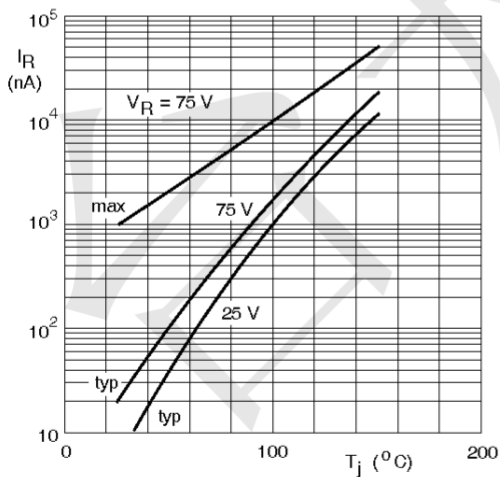


Maximum permissible continuous forward current as a function of soldering point temperature.

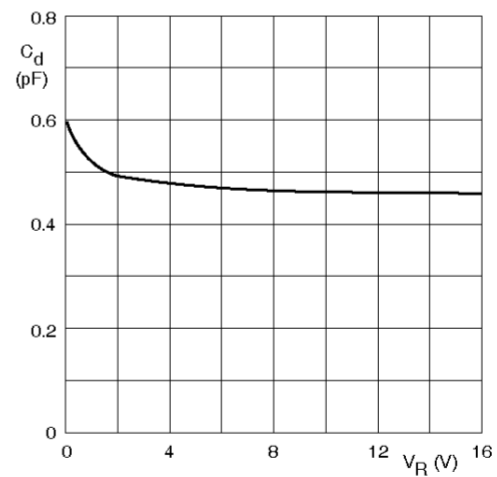


- (1) $T_j = 150^\circ\text{C}$; typical values.
- (2) $T_j = 25^\circ\text{C}$; typical values.
- (3) $T_j = 25^\circ\text{C}$; maximum values.

Forward current as a function of forward voltage.



Reverse current as a function of junction temperature.

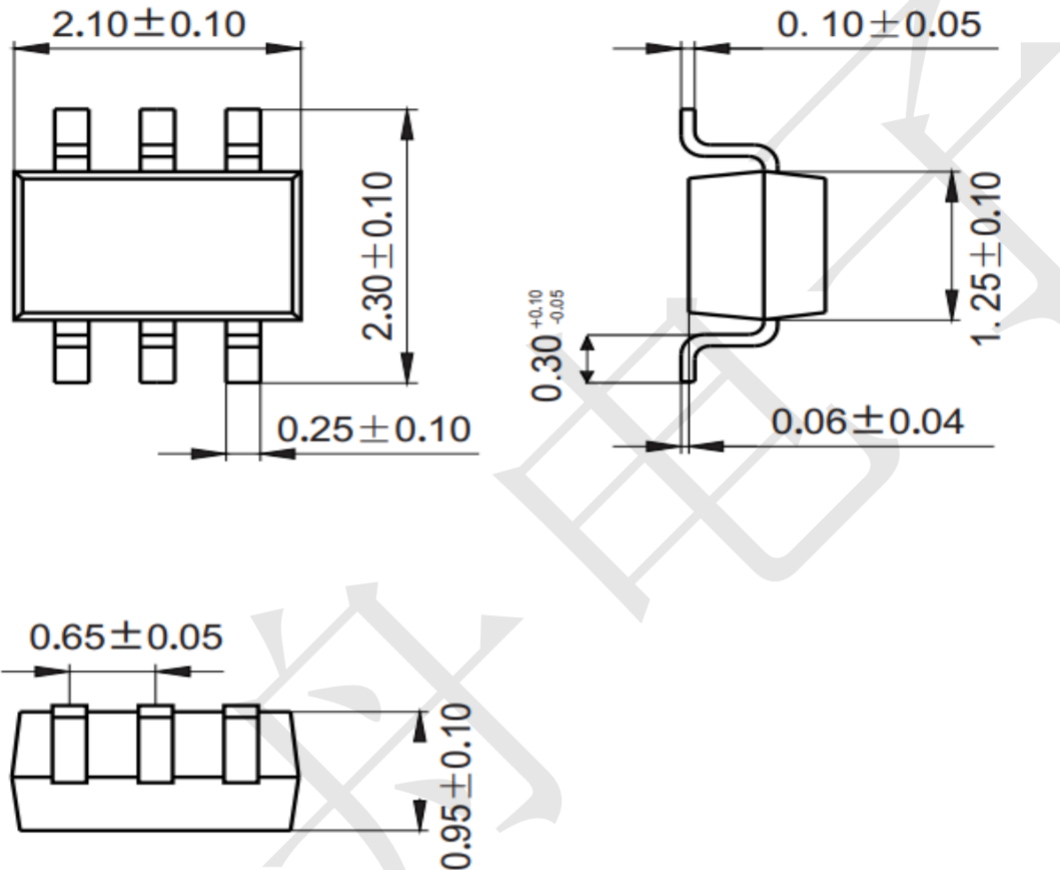


$f = 1\text{ MHz}$; $T_j = 25^\circ\text{C}$.

Diode capacitance as a function of reverse voltage; typical values.

Package information (Unit: mm)

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Mounting Pad Layout (Unit: mm)

